Dual Low-Voltage CMOS 2-to-4 Decoder/Demultiplexer

With 5V-Tolerant Inputs

The MC74LCX139 is a high performance, 2–to–4 decoder/demultiplexer operating from a 2.3 to 3.6 V supply. High impedance TTL compatible inputs significantly reduce current loading to input drivers while TTL compatible outputs offer improved switching noise performance. A V $_{\rm I}$ specification of 5.5 V allows MC74LCX139 inputs to be safely driven from 5 V devices. The MC74LCX139 is suitable for memory address decoding and other TTL level bus oriented applications.

The MC74LCX139 high–speed 2–to–4 decoder/demultiplexer accepts two binary weighted inputs (A0, A1) and, when enabled, provides four mutually exclusive active–LOW outputs. The LCX139 features an active low Enable input. All outputs will be HIGH unless En is LOW. The LCX139 can be used as an 8–output demultiplexer by using one of the active–LOW Enable inputs as the data input and the other Enable input as a strobe. The Enable inputs which are not used must be permanently tied to ground.

Current drive capability is 24 mA at the outputs.

- Designed for 2.3 to 3.6 V V_{CC} Operation
- 5 V Tolerant Inputs Interface Capability With 5 V TTL Logic
- LVTTL Compatible
- LVCMOS Compatible
- 24 mA Balanced Output Sink and Source Capability
- Near Zero Static Supply Current (10 μA) Substantially Reduces System Power Requirements
- Latchup Performance Exceeds 500 mA
- ESD Performance: Human Body Model >2000 V; Machine Model >200 V



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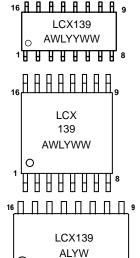
SO-16 D SUFFIX CASE 751B



TSSOP-16 DT SUFFIX CASE 948F







A = Assembly Location

WL, L = Wafer Lot YY, Y = Year WW, W = Work Week

ORDERING INFORMATION

Device	Package	Shipping
MC74LCX139D	SO-16	48 Units/Rail
MC74LCX139DR2	SO-16	2500 Units/Reel
MC74LCX139DT	TSSOP-16	96 Units/Rail
MC74LCX139DTEL	TSSOP-16	2000 Units/Reel
MC74LCX139DTR2	TSSOP-16	2000 Units/Reel
MC74LCX139M	EIAJ SO-16	48 Units/Rail
MC74LCX139MEL	EIAJ SO-16	2000 Units/Reel

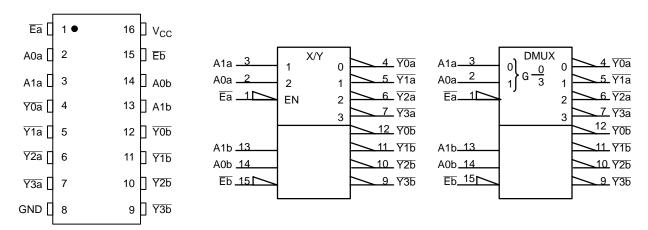


Figure 1. Pin Assignment

Figure 2. IEC Logic Diagram

PIN NAMES

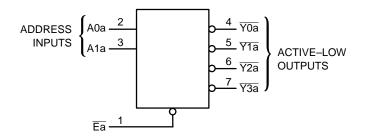
Pins	Function
A0n–A1n	Address Inputs
En	Enable Inputs
 Y0 n− Y3 n	Outputs

TRUTH TABLE

	Inputs	3		Out	puts	
Ē	A1	A0	<u>Y0</u>	<u>Y1</u>	<u>Y2</u>	<u>Y3</u>
Н	Х	Χ	Н	Н	Н	Н
L	L	L	L	Н	Н	н
L	L	Н	Н	L	Н	Н
L	Н	L	Н	Н	L	н
L	Н	Н	Н	Н	Н	L

H = High Voltage Level; L = Low Voltage Level;

Z = High Impedance State



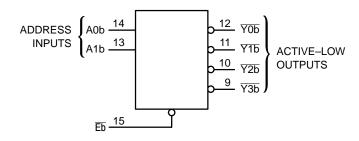


Figure 3. Logic Diagram

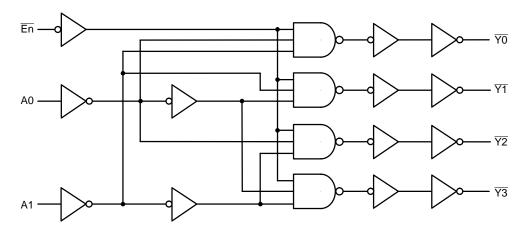


Figure 4. Expanded Logic Diagram (1/2 of Device)

MAXIMUM RATINGS

Symbol	Parameter	Value	Condition	Unit
V _{CC}	DC Supply Voltage	-0.5 to +7.0		V
VI	DC Input Voltage	$-0.5 \le V_1 \le +7.0$		V
Vo	DC Output Voltage	$-0.5 \le V_O \le V_{CC} + 0.5$	Output in HIGH or LOW State. (Note 1)	V
I _{IK}	DC Input Diode Current	-50	V _I < GND	mA
lok	DC Output Diode Current	-50	V _O < GND	mA
		+50	V _O > V _{CC}	mA
IO	DC Output Source/Sink Current	±50		mA
Icc	DC Supply Current Per Supply Pin	±100		mA
I _{GND}	DC Ground Current Per Ground Pin	±100		mA
T _{STG}	Storage Temperature Range	-65 to +150		°C

Maximum Ratings are those values beyond which damage to the device may occur. Exposure to these conditions or conditions beyond those indicated may adversely affect device reliability. Functional operation under absolute maximum–rated conditions is not implied. Functional operation should be restricted to the Recommended Operating Conditions.

RECOMMENDED OPERATING CONDITIONS

Symbol	Parameter		Min	Тур	Max	Unit
V _{CC}	Supply Voltage Ope Data Retention	erating n Only	2.0 1.5	2.3 to 3.3	3.6 3.6	V
VI	Input Voltage		0		5.5	V
Vo	Output Voltage (HIGH or LOW	State)	0		V _{CC}	V
I _{OH}	HIGH Level Output Current $ \begin{array}{c} V_{CC} = 3.0 \ V - \\ V_{CC} = 2.7 \ V - \\ V_{CC} = 2.3 \ V - \end{array} $	3.0 V			-24 -12 -8	mA
I _{OL}	LOW Level Output Current $ \begin{array}{c} V_{CC} = 3.0 \ V - \\ V_{CC} = 2.7 \ V - \\ V_{CC} = 2.3 \ V - \end{array} $	3.0 V			+24 +12 +8	mA
T _A	Operating Free-Air Temperature		-40		+85	°C
Δt/ΔV	Input Transition Rise or Fall Rate, V_{IN} from 0.8 V to 2.0 V, V	_{CC} = 3.0 V	0		10	ns/V

^{1.} I_O absolute maximum rating must be observed.

DC ELECTRICAL CHARACTERISTICS

			T _A = −40°C	$T_A = -40^{\circ}C$ to $+85^{\circ}C$	
Symbol	Characteristic	Condition	Min	Max	Unit
V _{IH}	HIGH Level Input Voltage (Note 2)	2.3 V ≤ V _{CC} ≤ 2.7 V	1.7		V
		2.7 V ≤ V _{CC} ≤ 3.6 V	2.0		
V _{IL}	LOW Level Input Voltage (Note 2)	2.3 V ≤ V _{CC} ≤ 2.7 V		0.7	V
		2.7 V ≤ V _{CC} ≤ 3.6 V		0.8	
V _{OH}	HIGH Level Output Voltage	$2.3 \text{ V} \le \text{V}_{CC} \le 3.6 \text{ V}; \text{I}_{OL} = 100 \mu\text{A}$	V _{CC} - 0.2		V
		$V_{CC} = 2.3 \text{ V; } I_{OH} = -8 \text{ mA}$	1.7		
		$V_{CC} = 2.7 \text{ V}; I_{OH} = -12 \text{ mA}$	2.2		
		$V_{CC} = 3.0 \text{ V; } I_{OH} = -18 \text{ mA}$	2.4		
		$V_{CC} = 3.0 \text{ V}; I_{OH} = -24 \text{ mA}$	2.2		
V _{OL}	LOW Level Output Voltage	$2.3 \text{ V} \le \text{V}_{CC} \le 3.6 \text{ V}; \text{I}_{OL} = 100 \mu\text{A}$		0.2	V
		V _{CC} = 2.3 V; I _{OL} = 8 mA		0.7	
		V _{CC} = 2.7 V; I _{OL} = 12 mA		0.4	
		V _{CC} = 3.0 V; I _{OL} = 16 mA		0.4	
		V _{CC} = 3.0 V; I _{OL} = 24 mA		0.55	
I _I	Input Leakage Current	$2.3 \text{ V} \le \text{V}_{CC} \le 3.6 \text{ V}; 0 \text{ V} \le \text{V}_{I} \le 5.5 \text{ V}$		±5	μΑ
I _{CC}	Quiescent Supply Current	$2.3 \le V_{CC} \le 3.6 \text{ V}; V_I = \text{GND or } V_{CC}$		10	μΑ
		$2.3 \le V_{CC} \le 3.6 \text{ V}; 3.6 \le V_{I} \text{ or } V_{O} \le 5.5 \text{ V}$		±10	1
ΔI_{CC}	Increase in I _{CC} per Input	$2.3 \le V_{CC} \le 3.6 \text{ V}; V_{IH} = V_{CC} - 0.6 \text{ V}$		500	μΑ

^{2.} These values of V_{I} are used to test DC electrical characteristics only.

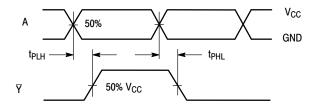
AC CHARACTERISTICS t_R = t_F = 2.5 ns; C_L = 50 pF; R_L = 500 Ω

			Limits					
			$T_A = -40$ °C to +85°C					
		V _{CC} = 3.0	V to 3.6 V	V _{CC} =	: 2.7 V	V _{CC} = 2.3	V to 2.7 V	
		C _L =	50 pF	C _L =	50 pF	C _L =	30pF	
Symbol	Parameter	Min	Max	Min	Max	Min	Max	Unit
t _{PLH}	Propagation Delay	0.8	6.2	1.0	7.3	0.8	9.3	ns
t _{PHL}	A to Y	0.8	6.2	1.0	7.3	0.8	9.3	ns
t _{PLH}	Propagation Delay	0.8	4.7	1.0	5.2	0.8	7.2	ns
t _{PHL}	E to Y	0.8	4.7	1.0	5.2	0.8	7.2	ns
t _{OSHL}	Output-to-Output Skew		1.0					ns
toslh	(Note 3)		1.0					ns

Skew is defined as the absolute value of the difference between the actual propagation delay for any two separate outputs of the same device.
 The specification applies to any outputs switching in the same direction, either HIGH-to-LOW (t_{OSHL}) or LOW-to-HIGH (t_{OSLH}); parameter guaranteed by design.

CAPACITIVE CHARACTERISTICS

Symbol	Parameter	Condition	Typical	Unit
C _{IN}	Input Capacitance	V_{CC} = 3.3 V, V_I = 0 V or V_{CC}	7	pF
C _{OUT}	Output Capacitance	V_{CC} = 3.3 V, V_{I} = 0 V or V_{CC}	8	pF
C _{PD}	Power Dissipation Capacitance	10MHz, V_{CC} = 3.3 V, V_I = 0 V or V_{CC}	25	pF



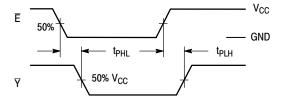
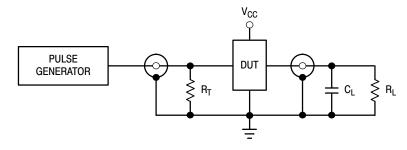


Figure 5. Waveform 1 Prop Delays

Figure 6. Waveform 2 Output Enable

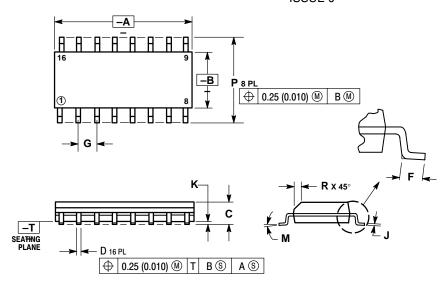


 C_L = 50 pF or equivalent (Includes jig and probe capacitance) R_L = R_1 = 500 Ω or equivalent R_T = Z_{OUT} of pulse generator (typically 50 $\Omega)$

Figure 7. Test Circuit

PACKAGE DIMENSIONS

SOIC-16 **D SUFFIX** CASE 751B-05 **ISSUE J**



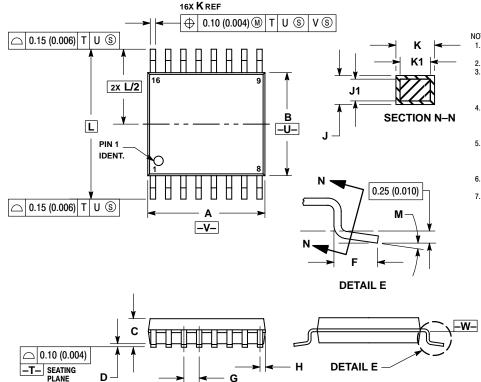
NOTES:

- DIMENSIONING AND TOLERANCING PER ANSI Y14.5M, 1982.
- T14-3M, 1902. CONTROLLING DIMENSION: MILLIMETER. DIMENSIONS A AND B DO NOT INCLUDE MOLD PROTRUSION.
- MAXIMUM MOLD PROTRUSION 0.15 (0.006) PER SIDE.
- PER SIDE.

 DIMENSION D DOES NOT INCLUDE DAMBAR PROTRUSION. ALLOWABLE DAMBAR PROTRUSION SHALL BE 0.127 (0.005) TOTAL IN EXCESS OF THE D DIMENSION AT MAXIMUM MATERIAL CONDITION.

	MILLIN	IETERS	INC	HES	
DIM	MIN	MAX	MIN	MAX	
Α	9.80	10.00	0.386	0.393	
В	3.80	4.00	0.150	0.157	
С	1.35	1.75	0.054	0.068	
D	0.35	0.49	0.014	0.019	
F	0.40	1.25	0.016	0.049	
G	1.2	7 BSC	0.050 BSC		
J	0.19	0.25	0.008	0.009	
K	0.10	0.25	0.004	0.009	
M	0°	7°	0°	7°	
Р	5.80	6.20	0.229	0.244	
R	0.25	0.50	0.010	0.019	

TSSOP-16 **DT SUFFIX** CASE 948F-01 **ISSUE O**



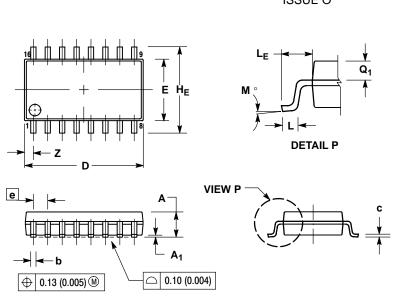
NOTES:

- DIMENSIONING AND TOLERANCING PER ANSI Y14.5M, 1982.
- Y14.5M, 1982.
 CONTROLLING DIMENSION: MILLIMETER.
 DIMENSION A DOES NOT INCLUDE MOLD FLASH.
 PROTRUSIONS OR GATE BURRS. MOLD FLASH OR
 GATE BURRS SHALL NOT EXCEED 0.15 (0.006) PER
- DIMENSION B DOES NOT INCLUDE INTERLEAD FLASH OR PROTRUSION. INTERLEAD FLASH OR PROTRUSION SHALL NOT EXCEED 0.25 (0.010) PER SIDE.
- 0.25 (0.010) PER SIDE.
 DIMENSION K DOES NOT INCLUDE DAMBAR
 PROTRUSION. ALLOWABLE DAMBAR PROTRUSION
 SHALL BE 0.08 (0.003) TOTAL IN EXCESS OF THE K
 DIMENSION AT MAXIMUM MATERIAL CONDITION.
- TERMINAL NUMBERS ARE SHOWN FOR REFERENCE ONLY.
- DIMENSION A AND B ARE TO BE DETERMINED AT DATUM PLANE -W-.

	MILLIN	IETERS	INC	HES
DIM	MIN	MAX	MIN	MAX
Α	4.90	5.10	0.193	0.200
В	4.30	4.50	0.169	0.177
С		1.20		0.047
D	0.05	0.15	0.002	0.006
F	0.50	0.75	0.020	0.030
G	0.65	BSC	0.026 BSC	
Н	0.18	0.28	0.007	0.011
J	0.09	0.20	0.004	0.008
J1	0.09	0.16	0.004	0.006
K	0.19	0.30	0.007	0.012
K1	0.19	0.25	0.007	0.010
L	6.40 BSC		0.252	BSC
М	0°	8°	0°	8°

PACKAGE DIMENSIONS

SOIC EIAJ-16 M SUFFIX CASE 966-01 **ISSUE O**



- NOTES:
 1. DIMENSIONING AND TOLERANCING PER ANSI Y14.5M, 1982.
 2. CONTROLLING DIMENSION: MILLIMETER.
 3. DIMENSIONS D AND E DO NOT INCLUDE MOLD FLASH OR PROTRUSIONS AND ARE MEASURED AT THE PARTING LINE. MOLD FLASH OR PROTR
- PROTRUSIONS SHALL NOT EXCEED 0.15 (0.006)
 PER SIDE.

 4. TERMINAL NUMBERS ARE SHOWN FOR
 REFERENCE ONLY.

 5. THE LEAD WIDTH DIMENSION (b) DOES NOT
 INCLUDE DAMBAR PROTRUSION. ALLOWABLE
 DAMBAR PROTRUSION SHALL BE 0.08 (0.003)
 TOTAL IN EXCESS OF THE LEAD WIDTH
 DIMENSION AT MAXIMUM MATERIAL CONDITION.
 DAMBAR CANNOT BE LOCATED ON THE LOWER
 RADIUS OR THE FOOT. MINIMUM SPACE
 BETWEEN PROTRUSIONS AND ADJACENT LEAD
 TO BE 0.46 (0.018). TO BE 0.46 (0.018).

	MILLIMETERS		INC	HES
DIM	MIN	MAX	MIN	MAX
Α		2.05		0.081
A ₁	0.05	0.20	0.002	0.008
b	0.35	0.50	0.014	0.020
С	0.18	0.27	0.007	0.011
D	9.90	10.50	0.390	0.413
E	5.10	5.45	0.201	0.215
е	1.27	BSC	0.050 BSC	
HE	7.40	8.20	0.291	0.323
L	0.50	0.85	0.020	0.033
LE	1.10	1.50	0.043	0.059
M	0 °	10°	0 °	10°
Q ₁	0.70	0.90	0.028	0.035
Z		0.78		0.031

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